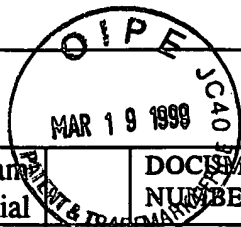


Section 2. Form PTO - 1449 (Modified) (ATTACHMENT)

FORM PTO-1449 U.S. DEPT. OF COMMERCE (Modified) PATENT AND TRADEMARK OFFICE	ATTY DOCKET NO. Nor-9	SERIAL NO. 09/247,413
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U.S. PATENT DOCUMENTS

Exam Initial	DOCUMENT NUMBER	DATE	PATENTEE	CLASS	SUB	FILING DATE IF APPROPR
	AA					
	AB					
	AC					
	AD					

FOREIGN PATENT OR PUBLISHED FOREIGN PATENT APPLICATION

Exam Initial	DOCUMENT NUMBER	DATE	COUNTRY	CLASS	SUB	TRANSLATION YES NO
	AL					
	AM					
	AN					

OTHER PRIOR ART

Exam Initial	Author, Title, Date, Pertinent Pages, Etc
<i>NAH</i>	AP Fitzgerald, E.A. et al, 1988, Elimination of Interface Defects In Mismatched Epilayers By A Reduction In Growth Area, Appl. Phys. Lett 52 (18), pp 1496-1498.
<i>NAH</i>	AQ Tachikawa, M. et al, 1998, Reduction Of Dislocation Generation For Heteroepitaxial III-V/Si By Slow Cooling, Journal of Crystal Growth 183, pp 89-94.
<i>NAH</i>	AR Tachikawa M. et al, 1990, Dislocation Generation Of GaAs on Si In the Cooling Stage, Appl. Phys. Lett. (56), pp 2225-2227
<i>NAH</i>	AS Ejeckam, F. et al, 1997, Dislocation-free InSb Grown on GaAs Compliant Universal Substrates, Appl. Phys. Lett., Vol 71, No. 6, pp 776-778.
<i>NAH</i>	AT Ejeckam, F. et al, 1997, Lattice Engineered Compliant Substrate For Defect-free Heteroepitaxial Growth, Appl. Phys. Lett. 70 (13), pp 1685-1687.
<i>NAH</i>	AU Zhu, A. et al, 1997, Wafer Bonding Technology and Its Applications in Optoelectronic Devices and Materials, IEEE Journal of Selected Topics in Quantum Electronics, Vol 3, No. 3, pp 927-935.
EXAMINER <i>Matthew D. Ouellet</i>	
DATE CONSIDERED <i>1/5/99</i>	